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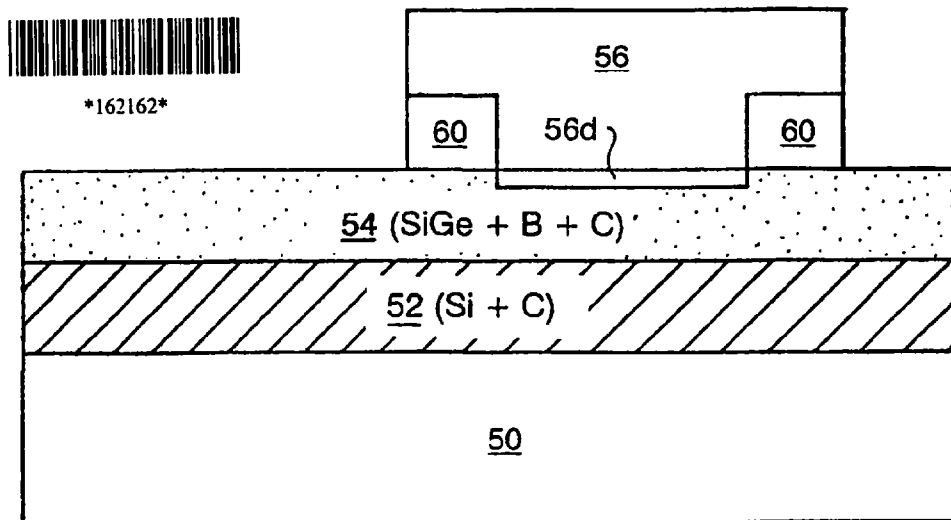
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(54) Title: SILICON GERMANIUM BIPOLAR TRANSISTOR



(57) Abstract: A SiGe bipolar transistor containing substantially no dislocation defects present between the emitter and collector region and a method of forming the same are provided. The SiGe bipolar transistor includes a collector region (52) of a first conductivity type; a SiGe base region (54) formed on a portion of said collector region (52); and an emitter region (56) of said first conductivity type formed over a portion of said base region (54), wherein said collector region (52) and said base region (54) include carbon continuously therein. The SiGe base region (54) is further doped with boron.

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